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(71) Applicant *(for all designated States except US)*: **S.O.I.TEC SILICON ON INSULATOR TECHNOLOGIES** [FR/FR]; Parc Technologique des Fontaines, Chemin des Franques, F-38190 Bernin (FR).

(72) Inventors; and

(75) Inventors/Applicants *(for US only)*: **LETERTRE, Fabrice** [FR/FR]; 33 quai Jongkind, F-38000 GRENOBLE (FR). **GHYSELEN, Bruno** [FR/FR]; 58, rue Georges Maeder, F-38170 Seyssinet (FR). **RAYSSAC, Olivier** [FR/FR]; 7, chemin Chapitre, F-38100 Grenoble (FR).

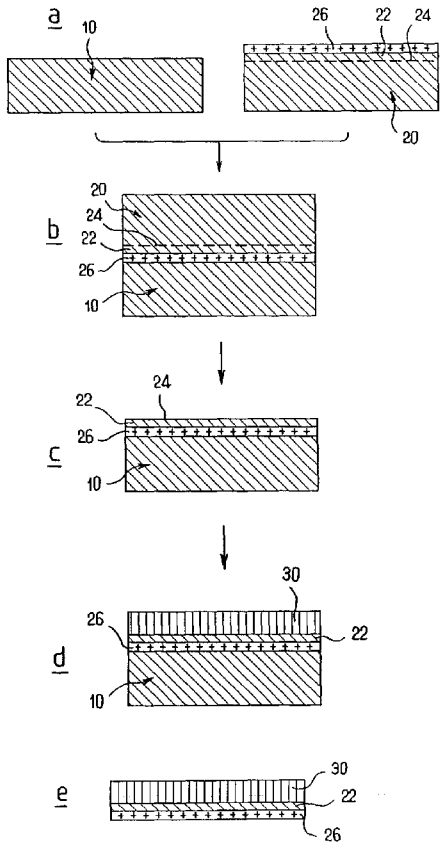
(74) Agents: **MARTIN, Jean-Jacques** et al.; Cabinet Regimbeau, 20, rue de Chazelles, F-75847 Paris Cedex 17 (FR).

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(54) Title: PROCESS FOR PREPARATION OF SEPARABLE SEMICONDUCTOR ASSEMBLIES, PARTICULARLY TO FORM SUBSTRATES FOR ELECTRONICS, OPTOELECTRONICS AND OPTICS



(57) Abstract: The invention propoeses processes for the preparation of an assembly (10, 12, 22, 30) based on semiconductors comprising a first layer such as a thin layer (22). A process comprises the followingsteps: form an interface layer (26) on only one (22) of the two layers, bring the layer on which the interface layer is formed and the other exposed layer into contact with each other, the interface layer (26) being chosen as a function of the material in the exposed layer to form a bonding interface that can be separated under the action of stresses applied after exposure to temperatures within a predetermined range. Application to the manufacture of substrates that can be separated from the support in the fields of electronics, optoelectronics or optics.

WO 03/063214 A2

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